

In the Specification:

Please replace paragraph [0026] with the following replacement paragraph:

[0026] As shown and described herein, like elements are shown by like numerals throughout. FIG. 2 is a cross-sectional view illustrating a preliminary stage in a patterning process according to an embodiment of the invention. As shown in FIG. 2, a patterned photoresist layer 10 is provided, overlying a layered stack to be patterned, including an anti-reflective coating (ARC) 11, a hardmask layer 15, an upper, heavily doped, polysilicon layer 12, having a dopant concentration, illustratively, of between about 10^{18}cm^{-3} and 10^{21}cm^{-3} , and a lower, lightly doped or "undoped" polysilicon layer 13, having a dopant concentration of less than about 10^{16}cm^{-3} , illustratively. At a critical dimension of 30 nm to 60 nm, such being the width of the photoresist pattern 10, the upper polysilicon layer 12 has a thickness 16 of about 50 nm. The lower polysilicon layer 13 can be an essentially "undoped" layer, which may or may not contain a slight dopant concentration. The lower polysilicon layer 13 can have a dopant concentration such as obtained by depositing polysilicon without intentionally doping the material. Alternatively, that layer 13 can be a lightly doped layer, typically having a dopant concentration that is two or more orders of magnitude lower than the dopant concentration of the upper layer 12. The lower polysilicon layer 13 has a thickness 21 of between about 50 nm and 100 nm.